

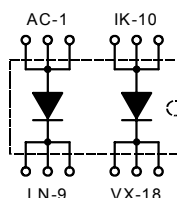
Fast Recovery Epitaxial Diode (FRED)

PSEI 2x101

$I_{FAVM} = 2 \times 96 \text{ A}$
 $V_{RRM} = 600 \text{ V}$
 $t_{rr} = 35 \text{ ns}$

Preliminary Data Sheet

V_{RSM} (V)	V_{RRM} (V)	Type
600	600	PSEI 2x101/06



Symbol	Test Conditions	Maximum Ratings	
I_{FRMS}	$T_{VJ} = T_{VJM}$	150	A
I_{FAVM}^*	$T_C = 70^\circ\text{C}$, rectangular, $d=0.5$	96	A
I_{FRM}	$t_p < 10\mu\text{s}$; rep. rating, pulse width limited by T_{VJM}	TBD	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	1200	A
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1300	A
	$T_{VJ} = 125^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	1080	A
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1170	A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	7200	A^2s
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	7100	A^2s
	$T_{VJ} = 125^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	5800	A^2s
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	5700	A^2s
T_{VJ}		-40... + 150	$^\circ\text{C}$
T_{VJM}		150	$^\circ\text{C}$
T_{stg}		-40... + 150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$	2500	V~
	$I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	3000	V~
M_d	Mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
Weight	typ.	24	g

Symbol	Test Conditions	Characteristic Value	
I_R	$T_{VJ} = 25^\circ\text{C}$, $V_R = V_{RRM}$	max.	3 mA
	$T_{VJ} = 25^\circ\text{C}$, $V_R = 0.8 \cdot V_{RRM}$	max.	1 mA
	$T_{VJ} = 125^\circ\text{C}$, $V_R = 0.8 \cdot V_{RRM}$	max.	20 mA
V_F	$I_F = 100 \text{ A}$, $T_{VJ} = 25^\circ\text{C}$	max.	1.25 V
V_{TO}	For power-loss calculations only	0.7	V
r_T		4.7	$\text{m}\Omega$
R_{thJC}	per diode; max.	0.5	K/W
R_{thCH}	per diode; typ.	0.05	K/W
I_{RM}	$I_F = 80 \text{ A}$; $-di_F/dt = 200 \text{ A}/\mu\text{s}$; $V_R = 100 \text{ V}$ $L \leq 0.05 \text{ mH}$; $T_{VJ} = 100^\circ\text{C}$	typ.	19 A
t_{rr}	$I_F = 1 \text{ A}$; $-di_F/dt = 400 \text{ A}/\mu\text{s}$; $V_R = 30 \text{ V}$; $T_{VJ} = 25^\circ\text{C}$	typ.	35 ns
d_s	Creeping distance on surface	11.2	mm
d_A	Creeping distance in air	11.2	mm
a	Max. allowable acceleration	50	m/s^2

Features

- 2 independent FRED in 1 package
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- Very short recovery time
- Soft recovery behaviour
- UL registered, E 148688

Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- Low noise switching
- Small and light weight

Data according to IEC 60747 refer to a single diode unless otherwise stated

* I_{FAVM} rating includes blocking losses at T_{VJM} ;
 $V_R = 0.8 V_{RRM}$; duty cycle $d = 0.5$

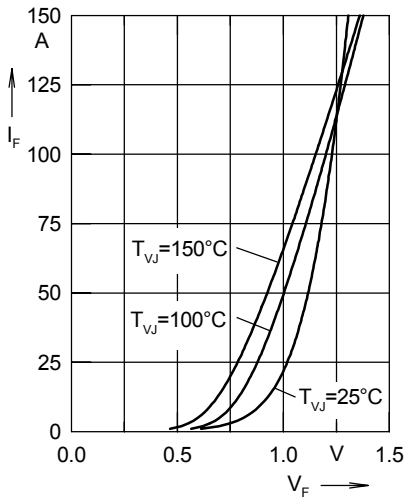


Fig. 1 Forward current I_F versus V_F

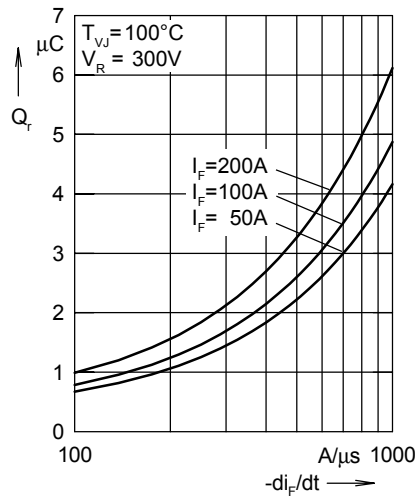


Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$

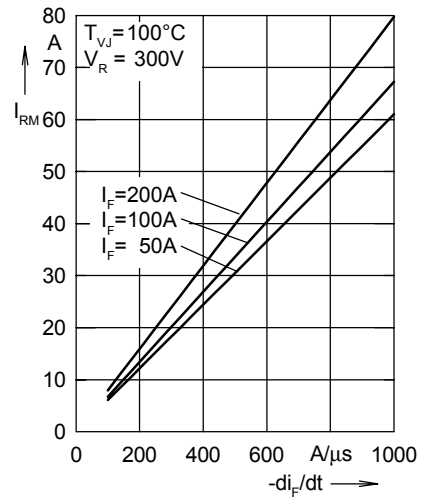


Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$

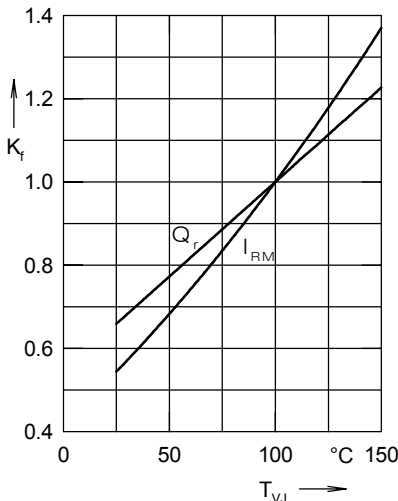


Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ}

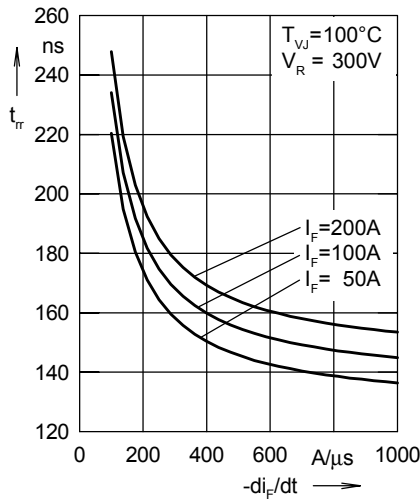


Fig. 5 Recovery time t_{tr} versus $-di_F/dt$

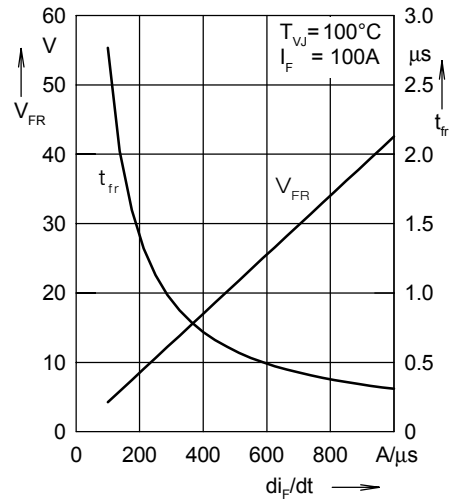


Fig. 6 Peak forward voltage V_{FR} and t_{tr} versus di_F/dt

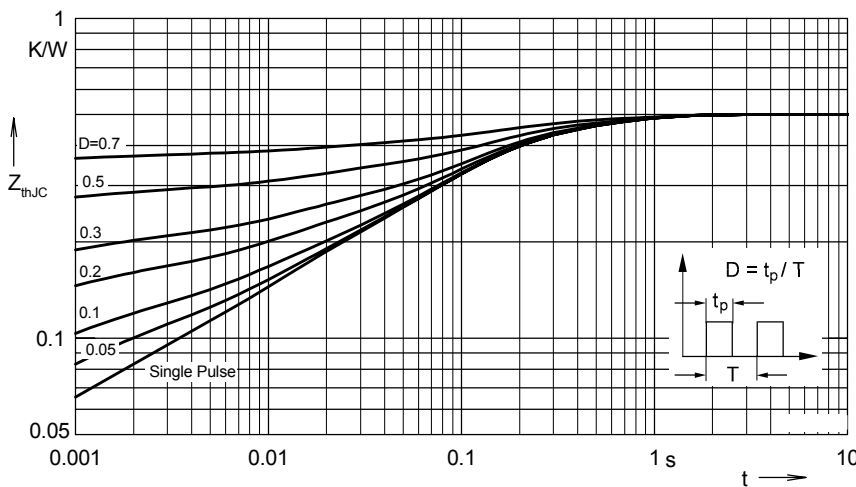


Fig. 7 Transient thermal impedance junction to case at various duty cycles

Package style and outline

Dimensions in mm (1mm = 0.0394")

